2SB1121

Bipolar Transistor -25V, -2A, Low VCE(sat) PNP Single PCP



http://onsemi.com

Applications

• Voltage regulators, relay drivers, lamp drivers, electrical equipment

Features

- Adoption of FBET, MBIT processes
- Large current capacity and wide SOA
- Low collector to emitter saturation voltage
- Fast switching speed
- Ultrasmall size making it easy to provide high-density, small-sized hybrid IC's

Specifications

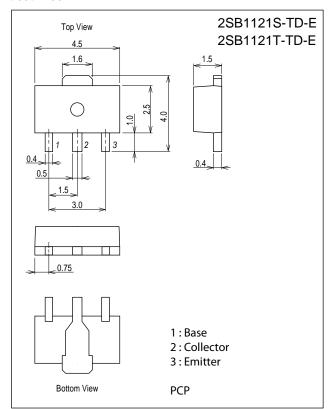
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector to Base Voltage	VCBO		-30	V
Collector to Emitter Voltage	VCEO		-25	V
Emitter to Base Voltage	V _{EBO}		-6	٧
Collector Current	IC		-2	Α
Collector Current (Pulse)	ICP		-5	Α

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Package Dimensions

unit: mm (typ) 7007B-004



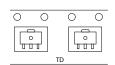
Product & Package Information

• Package

• JEITA, JEDEC : SC-62, SOT-89, TO-243

• Minimum Packing Quantity : 1,000 pcs./reel

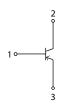
Packing Type: TD



Marking



Electrical Connection



Continued from preceding page.

Parameter	Symbol	Conditions	Ratings	Unit
Collector Dissipation	_		500	mW
	PC	When mounted on ceramic substrate (250mm ² ×0.8mm)	1.3	W
Junction Temperature	Тј		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

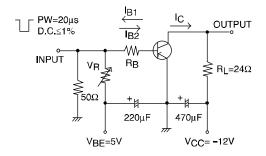
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			11.2
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =-20V, I _E =0A			-0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =-4V, I _C =0A			-0.1	μΑ
DC Current Gain	hFE1	V _{CE} =-2V, I _C =-100mA	140*		400*	
	hFE2	V _{CE} =-2V, I _C =-1.5A	65			
Gain-Bandwidth Product	fŢ	V _{CE} =-10V, I _C =-50mA		150		MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		32		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)	I _C =-1.5A, I _B =-75mA		-0.35	-0.6	V
Base to Emitter Saturation Voltage	V _{BE} (sat)	I _C =-1.5A, I _B =-75mA		-0.85	-1.2	V
Collector to Base Breakdown Voltage	V(BR)CBO	I _C =-10μA, I _E =0A	-30			V
Collector to Emitter Breakdown Voltage	V(BR)CEO	IC=-1mA, RBE=∞	-25			V
Emitter to Base Breakdown Voltage	V(BR)EBO	I _E =-10μA, I _C =0A	-6			V
Turn-ON Time	ton			60		ns
Storage Time	t _{stg}	See specified Test Circuit		350		ns
Fall Time	tf			25		ns

^{*:} The 2SB1121 is classified by 100mA hFE as follows:

Rank	S	T
$h_{ ext{FE}}$	140 to 280	200 to 400

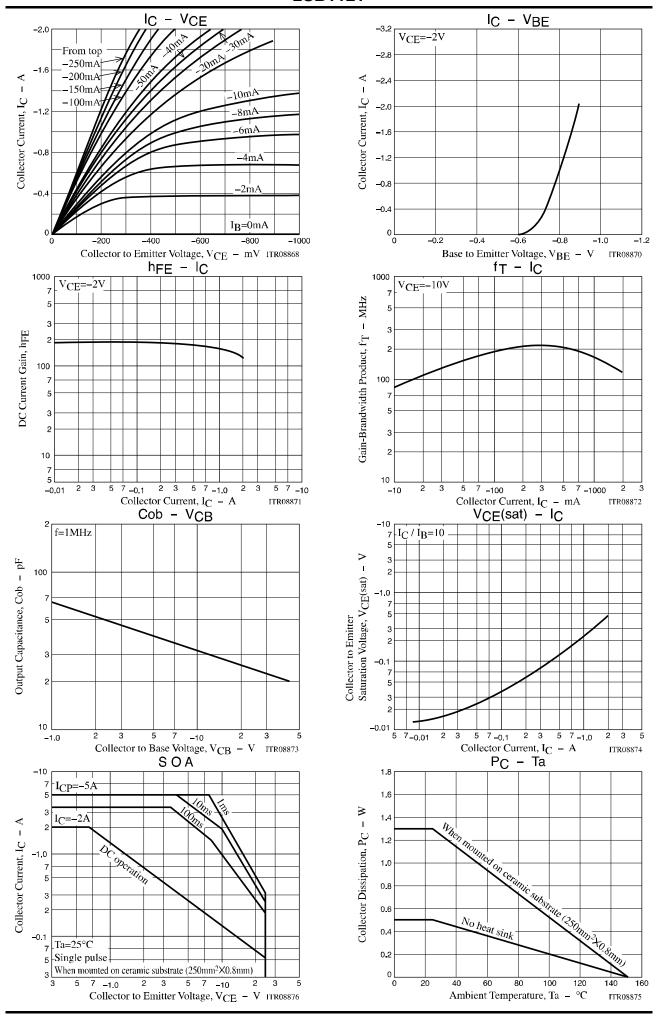
Switching Time Test Circuit



 $I_{C}=20I_{B1}=-20I_{B2}=-0.5A$

Ordering Information

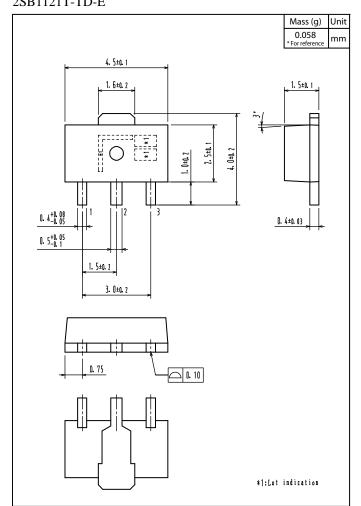
Device	Package	Shipping	Memo
2SB1121S-TD-E 2SB1121T-TD-E	PCP	1,000pcs./reel	Pb-Free

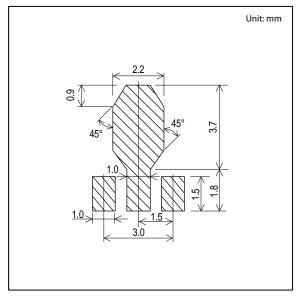


Outline Drawing

2SB1121S-TD-E 2SB1121T-TD-E

Land Pattern Example





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